



**CEDM7001E**

**SURFACE MOUNT  
N-CHANNEL  
ENHANCEMENT-MODE  
SILICON MOSFET**

**TLP** Tiny Leadless Package



**SOT-883L CASE**

**MARKING CODE: CEDM7001E: E**

# Central<sup>TM</sup> Semiconductor Corp.

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CEDM7001E is an Enhancement-mode N-Channel Field Effect Transistor, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers Low  $r_{DS(on)}$  and Low Theshold Voltage.

**FEATURES:**

- Power Dissipation 100mW
- Low Package Profile, 0.4mm
- Low  $r_{DS(on)}$
- Low Threshold Voltage
- Logic Level Compatible
- Small, TLP<sup>TM</sup> 1x0.6mm, SOT-883L Leadless Surface Mount Package

**APPLICATIONS:**

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Powered Portable Equipment

**MAXIMUM RATINGS** ( $T_A=25^\circ\text{C}$ )

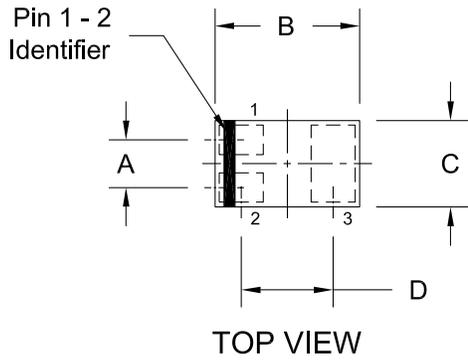
Drain-Source Voltage  
Gate-Source Voltage  
Continuous Drain Current (Steady State)  
Continuous Drain Current  
Power Dissipation  
Operating and Storage  
Junction Temperature

SYMBOL		UNITS
$V_{DS}$	20	V
$V_{GS}$	10	V
$I_D$	100	mA
$I_D$	200	mA
$P_D$	100	mW
$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

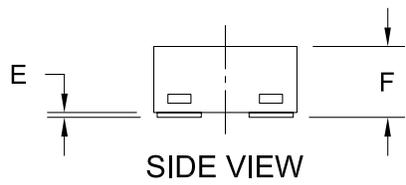
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_{GSSF}$	$V_{GS}=10\text{V}, V_{DS}=0\text{V}$			1.0	$\mu\text{A}$
$I_{GSSR}$	$V_{GS}=10\text{V}, V_{DS}=0\text{V}$			1.0	$\mu\text{A}$
$I_{DSS}$	$V_{DS}=20\text{V}, V_{GS}=0\text{V}$			1.0	$\mu\text{A}$
$BV_{DSS}$	$V_{GS}=0\text{V}, I_D=100\mu\text{A}$	20			V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.6		0.9	V
$r_{DS(ON)}$	$V_{GS}=4.0\text{V}, I_D=100\text{mA}$		1.0	2.0	$\Omega$
$Y_{fs}$	$V_{DS}=10\text{V}, I_D=100\text{mA}$	100			mS
$C_{rss}$	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$			TBD	pF
$C_{iss}$	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$			TBD	pF
$C_{oss}$	$V_{DS}=3.0\text{V}, V_{GS}=0, f=1.0\text{MHz}$			TBD	pF
$t_{on}$	$V_{DD}=3.0\text{V}, V_{GS}=2.5\text{V}, I_D=10\text{mA}$			TBD	ns
$t_{off}$	$V_{DD}=3.0\text{V}, V_{GS}=2.5\text{V}, I_D=10\text{mA}$			TBD	ns

SOT-883L - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.014		0.35	
B	0.037	0.041	0.95	1.05
C	0.022	0.026	0.55	0.65
D	0.026		0.65	
E	0.000	0.002	0.00	0.05
F	0.012	0.016	0.30	0.40
G	0.005	0.007	0.13	0.18
H	0.008	0.012	0.20	0.30
J	0.018	0.022	0.45	0.55
K	0.008	0.012	0.20	0.30

SOT-883L (REV:R2)



**LEAD CODE:**

- 1) GATE
- 2) SOURCE
- 3) DRAIN

